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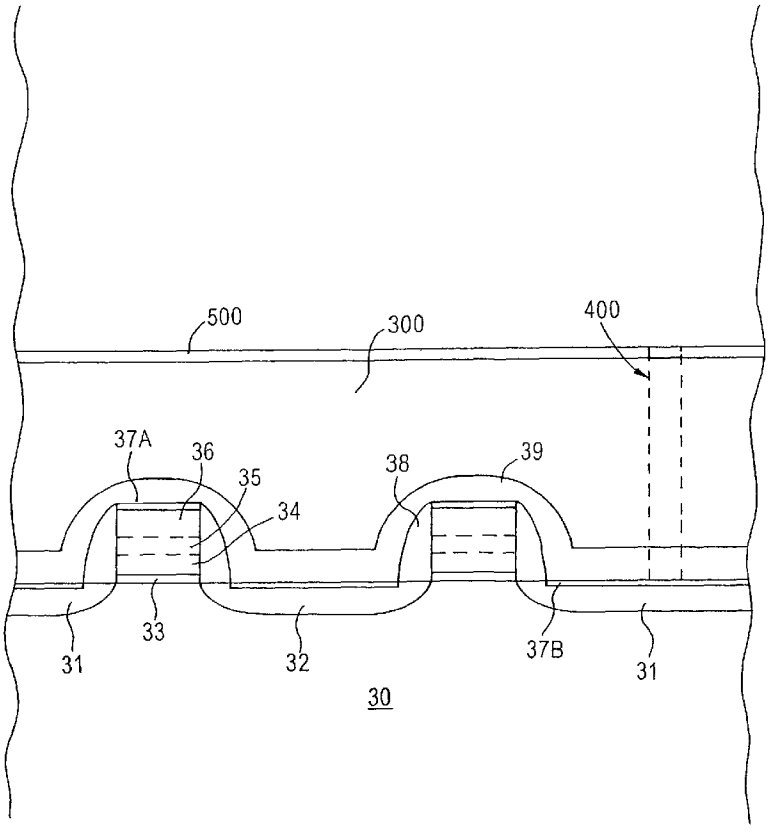
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(54) Title: PECVD SILICON-RICH OXIDE LAYER FOR REDUCED UV CHARGING IN AN EEPROM



(57) Abstract: A Si-rich silicon oxide layer (500) having reduced UV transmission is deposited by PECVD, on an interlayer dielectric (300) , prior to metallization, thereby reducing V_t. Embodiments include depositing a UV opaque Si-rich silicon oxide layer (500) having a refractive index (R.I.) of 1.7 to 2.0. The Si-rich silicon oxide layer (SiRo) reduces UV cell charging problems in the fabrication of EEPROM flash memories.

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